Friedrich-Schiller-Universität Jena

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### **Connection of Field Solvers: Lenses and Microstructures**

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## **Background: Systems Containing Lenses and Microstructures**



# **Motivation: Connection of Field Solvers**



- Ray tracing is limited, because diffraction, polarization, coherence is not included.
- > Vectorial physical-optics modeling is desired, but FEM, FMM, FDTD etc. are slow.
- An efficient and accurate physical-optics modeling with fully vectorial effects is desired.
- Therefore, connection of the field solvers, e.g. lenses and microstructures, is one desired option to model the system efficiently and accurately, with fully vectorial effect.

# Task: Ultraviolet (UV) Microscopy for Inspection of Wafer Structure



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x

# Task: Ultraviolet (UV) Microscopy for Inspection of Wafer Structure



 $x \xrightarrow{x} \xrightarrow{z} z$ 

# **Fully Vectorial Modeling in the Framework of Field Tracing**



Talk 22: Z. Wang et.al

## **B** Operator for Lens by LPIA



R. Shi, C. Hellmann, and F. Wyrowski, J. Opt. Soc. Am. A 36, (2019).

2<sup>out</sup>

 $\epsilon_{II}$ 

 $\oint_{\hat{z}} \hat{x}$ 

## **B** Operator for Lens by LPIA: Validation on Curved Surface

Results by FEM via JCMSuite





R. Shi, C. Hellmann, and F. Wyrowski, J. Opt. Soc. Am. A **36**, (2019).

## **B** Operator for Lens by LPIA: Validation on Plane

Results by FEM via JCMSuite





 $= \mathcal{P}^{\text{out}} \mathcal{B}^{\text{LPIA}} \mathcal{P}^{\text{in}}$ 

 $\mathcal{B}^{(1)}$ 

Time of LPIA+FSP: <1 s Time of FEM: ~20 mins

R. Shi, C. Hellmann, and F. Wyrowski, J. Opt. Soc. Am. A 36, (2019).

## **B** Operator for Microstructure by FMM







#### **Simulation Results via VirtualLab Fusion**

#### **Near and Far Field Images for TE and TM**

### **Near Field for Different Polarizations, without Evanescent Waves**



## **Far Field for Different Polarizations**



### **Comparison of Near and Far Field Images**

### **Comparison of the Near Field and Far Field Image**



#### **Far Field Image Sensitivity of Defects**

## Far Field Image Sensitivity V.S Defect of Height of PMMA



 The far field image profile has obvious change when the height of PMMA changes from ±20 nm.



## Far Field Image Sensitivity V.S Defect of Width of Gold Ridge



• The far field image profile changes but not so obviously, when the width of the gold ridge changes by +40 nm.



# **Summary and Conclusion**

- We connect the field solvers of lenses and microstructures in the framework of field tracing;
- We apply it to the UV microscopy of inspection of wafer structure.
- We find that,
  - the near and far field images for different polarized illuminations are different.
  - the far field image is not the directly magnified near field image in the TM case.
  - the far field image is more sensitive to the height of the PMMA compared to the width of the gold ridge.



### **Appendix Near Field with Evanescent Waves**

# Validation of LPIA



R. Shi, C. Hellmann, and F. Wyrowski, J. Opt. Soc. Am. A 36, (2019).

# Validation of LPIA



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#### **Near Field for Different Polarization with Evanescent Waves**



